

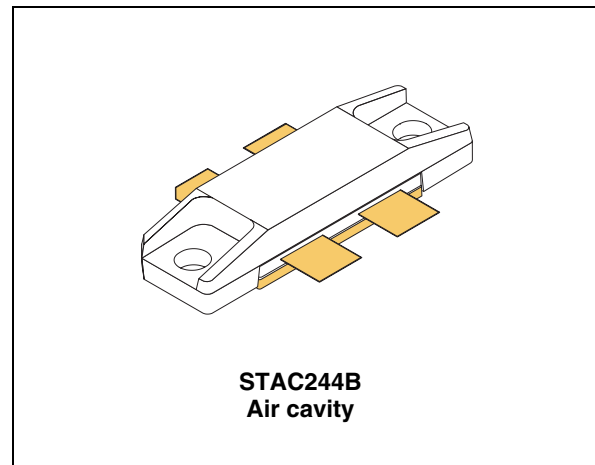
## HF/VHF/UHF RF power N-channel MOSFETs

### Features

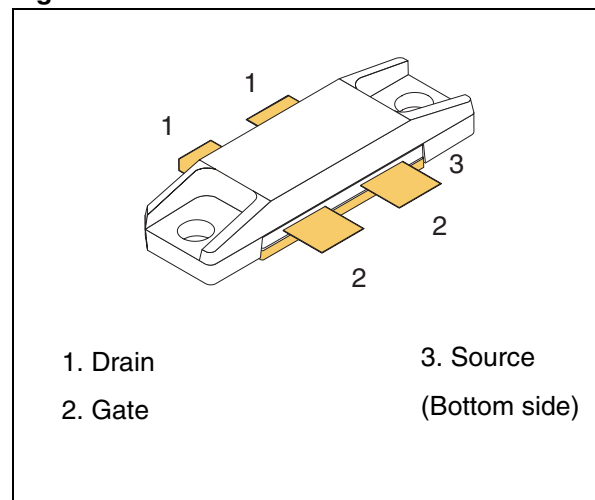
- Gold metallization
- Excellent thermal stability
- Common source push-pull configuration
- $P_{OUT} = 300\text{ W}$  min. with 20 dB gain @ 175 MHz
- In compliance with the 2002/95/EC European directive
- ST air cavity packaging technology - STAC™ package

### Description

The STAC2932B is a gold metallized N-channel MOS field-effect RF power transistor. It is intended for use in 50 V DC large signal applications up to 250 MHz. The STAC2932B benefits from the latest generation of efficient, patent-pending STAC™ package technology.



**Figure 1. Pin connection**



**Table 1. Device summary**

Order code	Marking	Base qty.	Package	Packaging
STAC2932B	STAC2932 <sup>(1)</sup>	20	STAC244B	Tray

1. For more details please refer to [Chapter 7: Marking, packing and shipping specifications](#).

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# 1 Electrical data

## 1.1 Maximum ratings

( $T_{\text{CASE}} = 25\text{ °C}$ )

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{(\text{BR})\text{DSS}}^{(1)}$	Drain source voltage	125	V
$V_{\text{DGR}}$	Drain-gate voltage ( $R_{\text{GS}} = 1\text{ M}\Omega$ )	125	V
$V_{\text{GS}}$	Gate-source voltage	$\pm 20$	V
$I_{\text{D}}$	Drain current	40	A
$P_{\text{DISS}}$	Power dissipation	625	W
$T_{\text{J}}$	Max. operating junction temperature	200	$^{\circ}\text{C}$
$T_{\text{STG}}$	Storage temperature	-65 to +150	$^{\circ}\text{C}$

1.  $T_{\text{J}} = 150\text{ °C}$

## 1.2 Thermal data

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{\text{thJC}}$	Junction - case thermal resistance	0.28	$^{\circ}\text{C/W}$

## 2 Electrical characteristics

$T_{CASE} = +25\text{ }^{\circ}\text{C}$

### 2.1 Static

**Table 4. Static (per side)**

Symbol	Test conditions			Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$	$I_{DS} = 100\text{ mA}$		125			V
$I_{DSS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 50\text{ V}$				50	$\mu\text{A}$
$I_{GSS}$	$V_{GS} = 20\text{ V}$	$V_{DS} = 0\text{ V}$				250	nA
$V_{GS(Q)}$	$V_{DS} = 10\text{ V}$	$I_D = 250\text{ mA}$		1.5	2.5	4.0	V
$V_{DS(ON)}$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}$				3.0	V
$G_{FS}$	$V_{DS} = 10\text{ V}$	$I_D = 5\text{ A}$		5			S
$C_{ISS}$	$V_{GS} = 0\text{ V}$ $V_{DS} = 50\text{ V}$ $f = 1\text{ MHz}$				468		pF
$C_{OSS}$					206		pF
$C_{RSS}$					16		pF

### 2.2 Dynamic

**Table 5. Dynamic**

Symbol	Test conditions	Min.	Typ.	Max.	Unit
$P_{OUT}$	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 2 \times 250\text{ mA}$ , $P_{IN} = 4\text{ W}$ , $f = 175\text{ MHz}$	300	390		W
$h_D$	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 2 \times 250\text{ mA}$ , $P_{IN} = 4\text{ W}$ , $f = 175\text{ MHz}$	55	68		%

### 3 Impedance

Figure 2. Current conventions

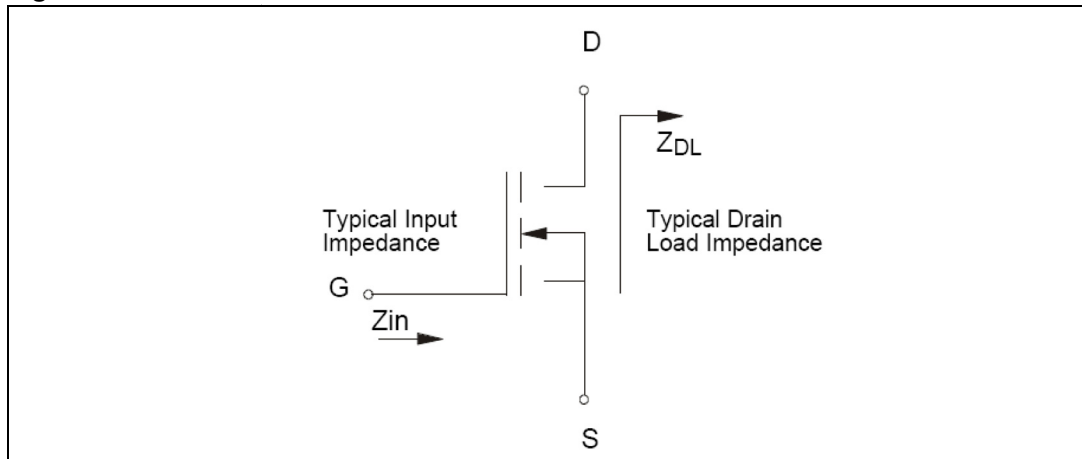


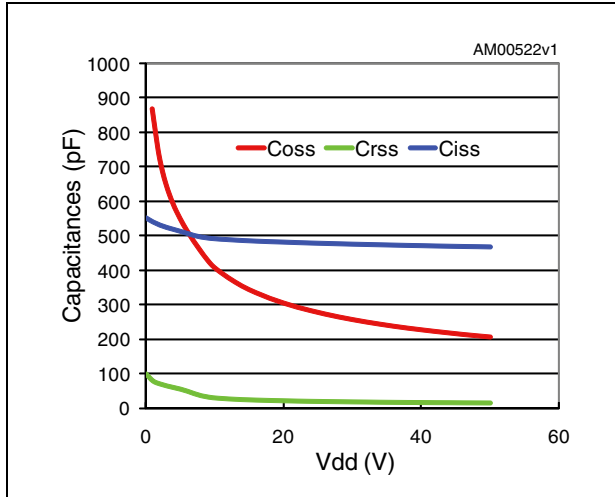
Table 6. Impedance data

Freq. (MHz)	$Z_{IN}$ ( $\Omega$ )	$Z_{DL}$ ( $\Omega$ )
175 MHz	$2.0 - j2.0$	$3.5 + j5.2$

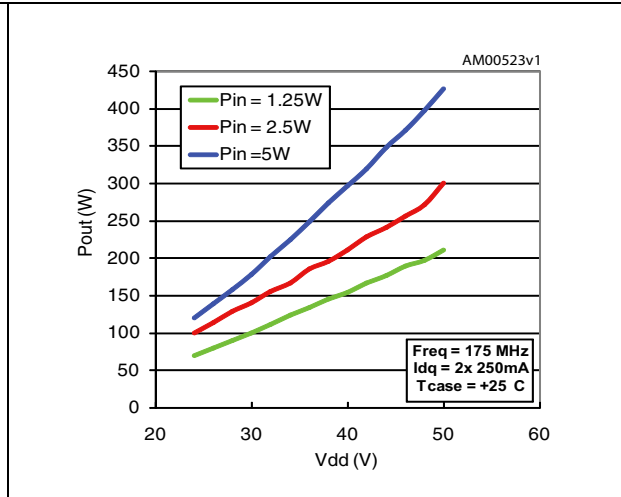
Note: Measured gate to gate and drain to drain, respectively.

# 4 Typical performance

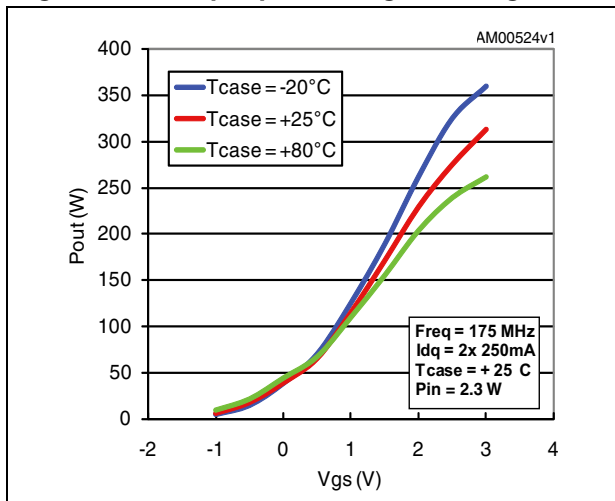
**Figure 3. Capacitances vs drain supply voltage**



**Figure 4. Output power vs drain supply voltage**



**Figure 5. Output power vs gate voltage**



**Figure 6. Output power vs input power**

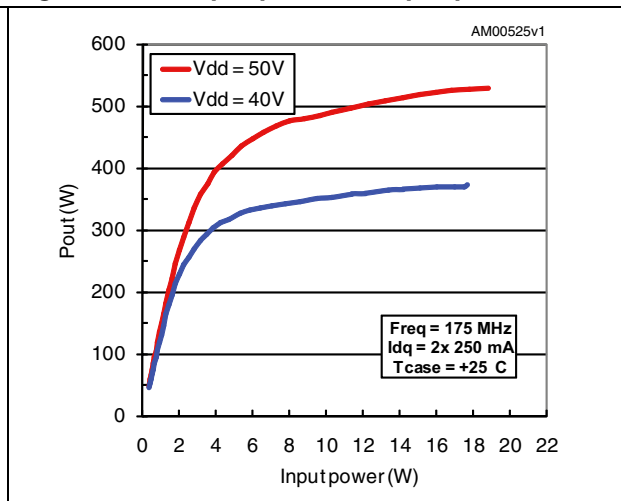


Figure 7. Output power vs input power and case temperature

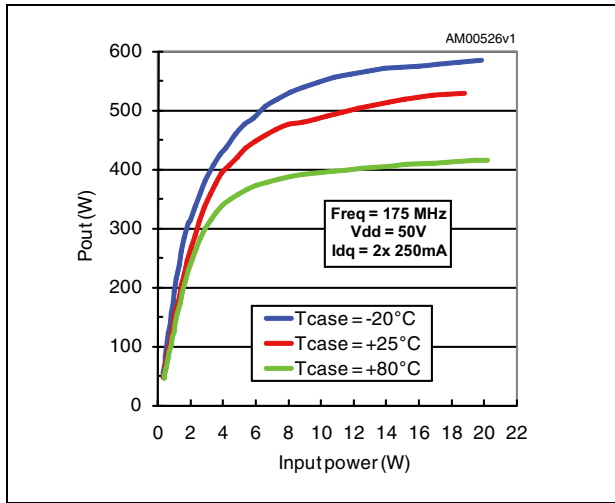
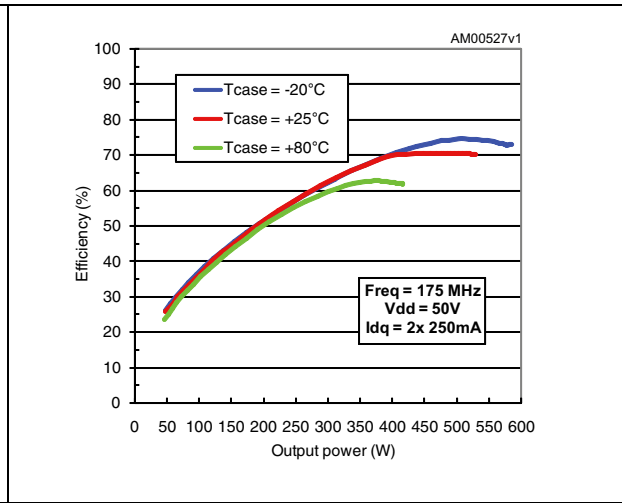


Figure 8. Efficiency vs output power and case temperature



# 5 Test circuit

Figure 9. 175 MHz test circuit schematic (production test circuit)

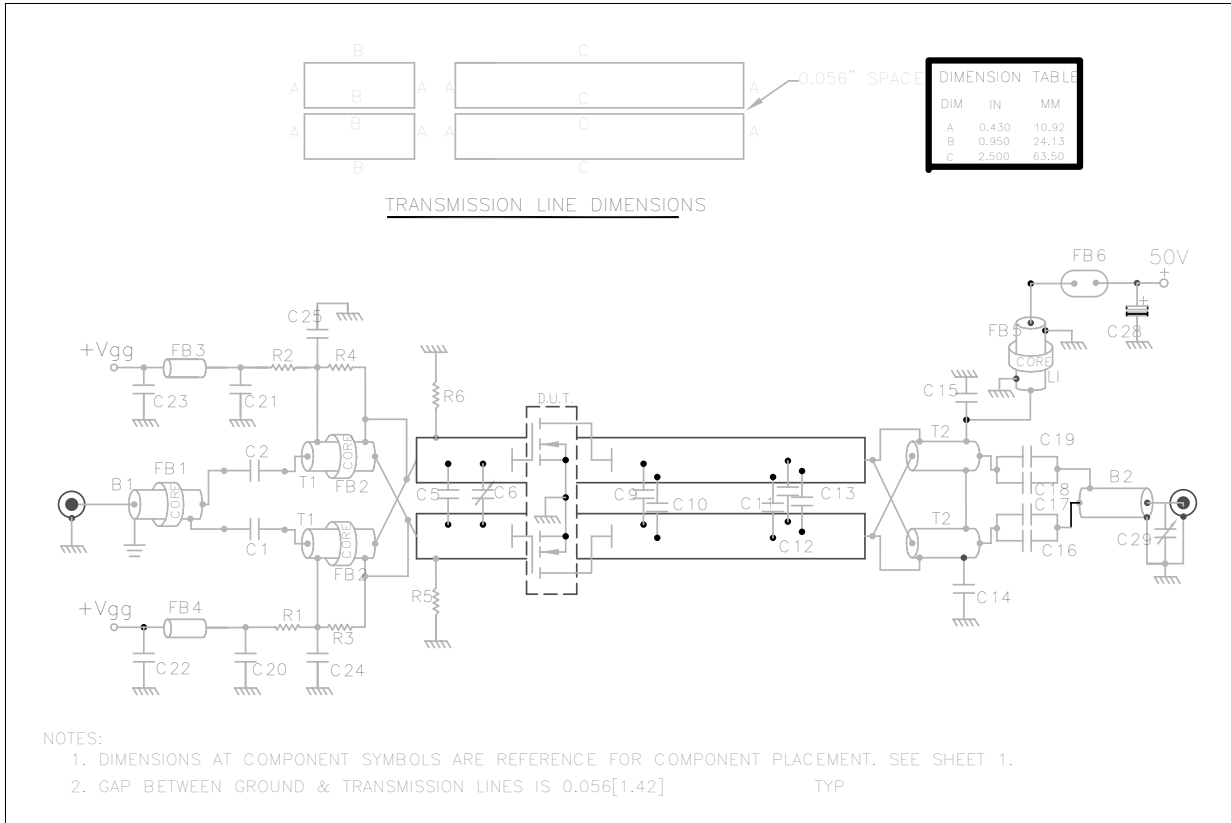


Table 7. 175 MHz test circuit component list

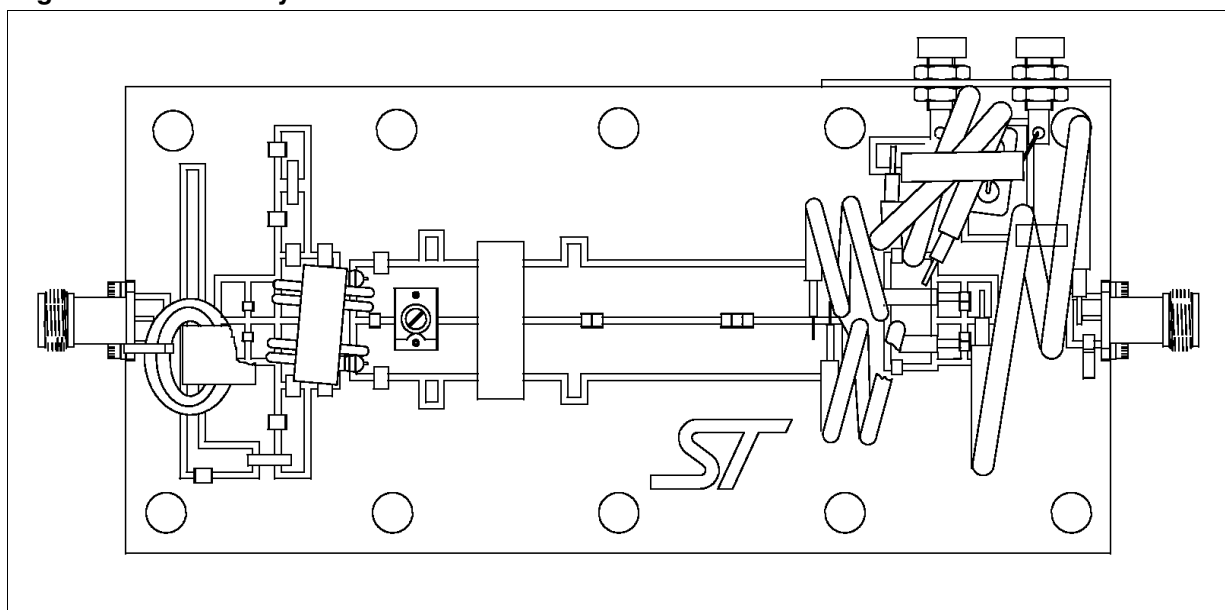
Component	Description
C1, C2, C14, C15, C24, C25	1200 pF ATC 700B chip capacitor
C5	75 pF ATC 100B chip capacitor
C6	ST406 variable capacitor
C9, C10	47 pF ATC 100B chip capacitor
C11, C12, C13	43 pF ATC 100B chip capacitor
C16, C18	470 pF ATC 100B chip capacitor
C17, C19, C20, C21	10,000 pF ATC 200B chip capacitor
C22, C23	0.1 μF 200 V chip capacitor
C28	10 μF 100 V electrolytic capacitor
C29	0.8 - 8 pF variable capacitor
R1, R2, R5, R6	430 Ω, 1/2 W chip resistor



Table 7. 175 MHz test circuit component list (continued)

Component	Description
R3, R4	270 Ω 1/2 W axial lead resistor
B1	RG-316 50 Ω 11.8" through ferrite toroidal
B2	RG-142 50 Ω 11.8"
T1	4:1, RG-316 25 Ω, 5.9", 2 turns thru ferrite core
T2	1:4, 25 Ω semi-rigid cable, OD.141", 5.9"
L1	λ/4 inductor, RG-142 50 Ω, 11.8", 3 turns thru ferrite toroid
FB1,FB5	ferrite toroidal
FB2, FB6	multi-aperture core
FB3, FB4	surface mount ferrite bead
PCB	Rogers ultralam 2000, Er 2.55, 0.060"

Figure 10. Circuit layout



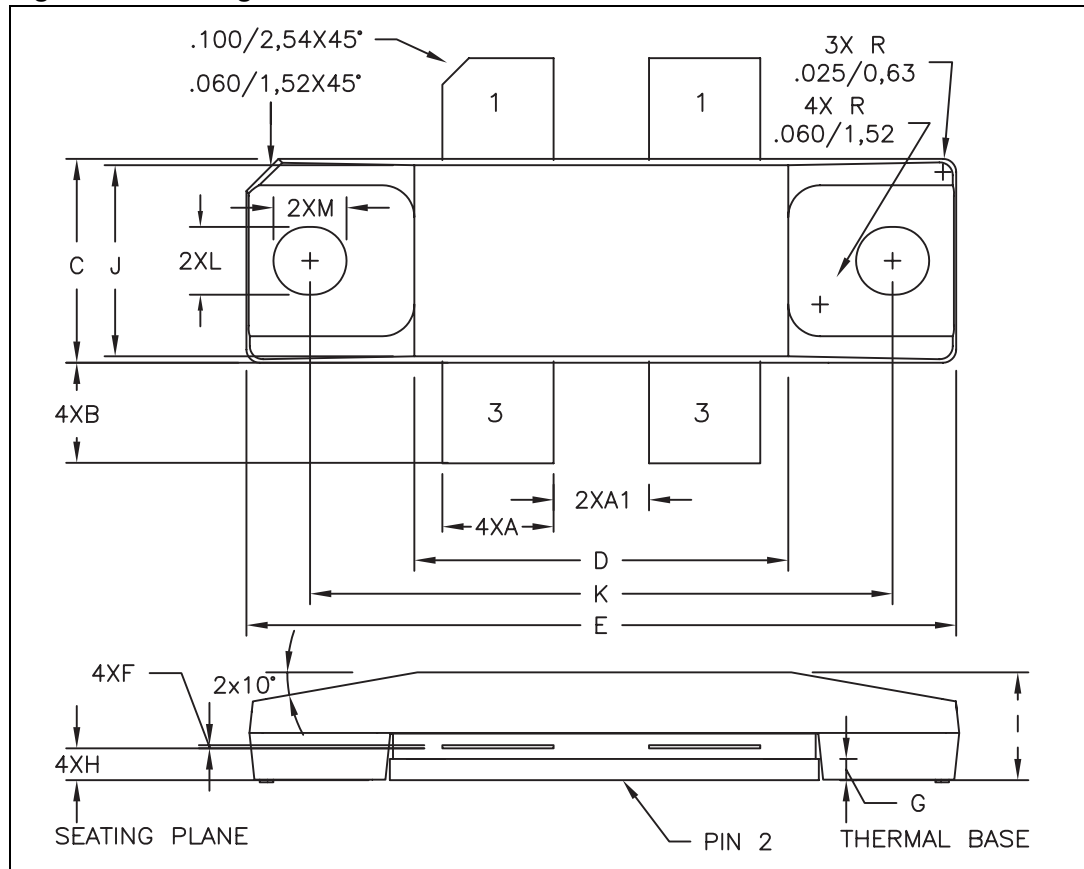
## 6 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 8. STAC244B mechanical data**

Dim.	mm.		
	Min.	Typ.	Max.
A	5.08		5.59
A1	4.32		4.83
B	4.32		5.33
C	9.65		9.91
D	17.78		18.08
E	33.88		34.19
F	0.10		0.15
G		1.02	
H	1.45		1.70
I	4.83		5.33
J	9.27		9.52
K	27.69		28.19
L	3.12	3.23	3.33
M	3.35	3.45	3.56

Figure 11. Package dimensions

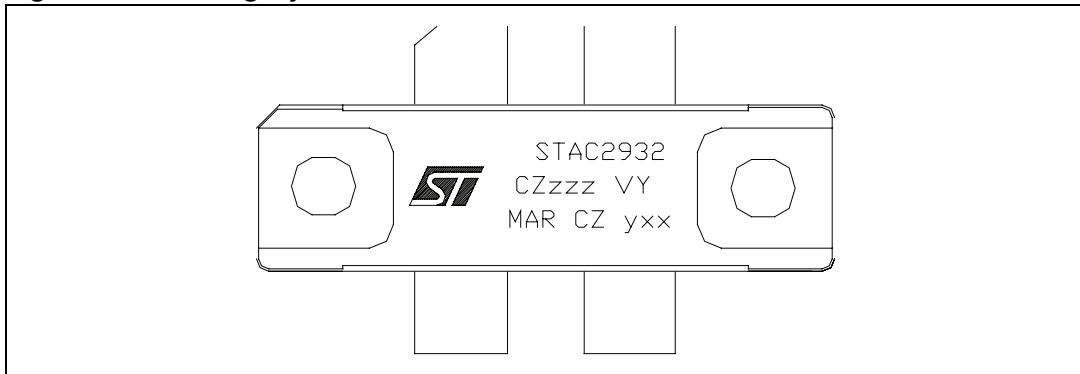


## 7 Marking, packing and shipping specifications

**Table 9. Packing and shipping specifications**

Order code	Packaging	Pcs per tray	Dry pack humidity	Lot code
STAC2932B	Tray	20	< 10 %	Not mixed

**Figure 12. Marking layout**



**Table 10. Marking specifications**

Symbol	Description
CZ	Assembly plant
xxx	Last 3 digits of diffusion lot
VY	Diffusion plant
MAR	Country of origin
CZ	Test and finishing plant
y	Assembly year
yy	Assembly week

## 8 Revision history

**Table 11. Document revision history**

Date	Revision	Changes
20-Mar-2009	1	First release.
29-Jun-2010	2	Updated features and description on cover page.
12-Aug-2011	3	Update figures on coverpage and <a href="#">Section 6: Package mechanical data</a> . Inserted <a href="#">Section 7: Marking, packing and shipping specifications</a> . Minor text changes.
05-Sep-2011	4	Update L and M dimensions <a href="#">Table 9 on page 12</a> .

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